

Please amend the subject application as follows:

IN THE CLAIMS

Please accept amended claims 1, 4, 6 and 7, and cancel claim 2:

1. (Currently amended) A plasma chamber comprising a lower electrode and an upper electrode, and used for dry-etching an LCD, comprising:

a main power supply comprising a main power source to generate a main voltage having a predetermined main frequency (ω_1) and a predetermined amplitude (E_1), and a first impedance matching circuit to impedance-match the main voltage;

a bias power supply comprising a bias power source to generate a bias voltage having a predetermined bias frequency (ω_2) and a predetermined amplitude (E_2), and a second impedance matching circuit to impedance-match the bias voltage;

at least one auxiliary power supply comprising an auxiliary power source to generate an auxiliary voltage having a predetermined frequency and a third impedance matching circuit to impedance-match the auxiliary voltage; and

a mixer connected to ~~both~~ the first impedance matching circuit, ~~and~~ the second impedance matching circuit, and the third impedance matching circuit, wherein the mixer receives and mixes the main voltage, ~~and~~ the bias voltage, and the auxiliary voltage, and outputs ~~the~~ a mixed voltage to one of the lower electrode and the upper electrode;

~~wherein the mixed voltage comprises $E_1 \cos(\omega_1 t)$ for generating plasma and $E_1 + (E_2 - E_1) \cos(\omega_2 t)$ for adjusting etching conditions when the main frequency is substantially larger than the bias frequency.~~

2. (Canceled)

3. (Original) The plasma chamber according to claim 1, wherein the mixer outputs the mixed voltage by adding the received voltages.

4. (Currently amended) The plasma chamber according to claim ~~[[2]]~~1, wherein the mixer outputs the mixed voltage by adding the received voltages.

5. (Original) The plasma chamber according to claim 1, wherein the bias frequency is lower than the main frequency.

6. (Currently amended) The plasma chamber according to claim ~~[[2]]~~1, wherein the bias frequency is lower than the main frequency.

7. (Currently amended) A plasma chamber comprising a lower electrode and an upper electrode, and used for dry-etching an LCD, comprising:

a main power supply comprising a main power source to generate a main voltage having a predetermined main frequency (ω_1) ~~and a predetermined amplitude (E_1)~~, and a first impedance matching circuit to impedance-match the main voltage;

a bias power supply comprising a bias power source to generate a bias voltage having a predetermined bias frequency (ω_2) ~~and a predetermined amplitude (E_2)~~, and a second impedance matching circuit to impedance-match the bias voltage;

at least one auxiliary power supply comprising an auxiliary power source to generate an auxiliary voltage having a predetermined frequency and a third impedance matching circuit to impedance-match the auxiliary voltage; and

a mixer connected to ~~both~~ the first impedance matching circuit and the second impedance matching circuit, and the third impedance matching circuit, wherein the mixer receives and mixes the main voltage and the bias voltage, and the auxiliary voltage, and outputs ~~the~~ a mixed voltage to one of the lower electrode and the upper electrode, and wherein the mixer prevents the main power source, ~~and~~ the bias power source, and the auxiliary power source from being directly connected to the lower electrode for simultaneously supplying AC power from the main, ~~and~~ bias, and auxiliary power sources to the lower electrode;

wherein the mixed voltage comprises $E_1 \cos(\omega_1 t)$ for generating plasma and $E_1 + (E_2 - E_1) \cos(\omega_2 t)$ for adjusting etching conditions when the main frequency is substantially larger than the bias frequency.